

ABSTRACT OF THE DISCLOSURE

A method for fabricating patterned resist masks. Firstly, a photoresist film is applied on a semiconductor substrate in a customary manner, which photoresist film is then exposed by means of customary techniques. In the development step, a rinsing medium containing a cationic surfactant is used. If the patterned resist is dried after development, the sidewalls of the resist webs are rendered hydrophobic by the cationic surfactant, so that the contact angle can be increased to values of approximately 90° , reducing capillary forces acting on the webs of the patterned resist to approximately zero. As a result, even in the case of single-layer resist films, the line width of the webs can be reduced without a line collapse being observed.